

Isc N-Channel MOSFET Transistor

SPP11N80C3

• FEATURES

- Ultra low effective capacitances
- Low gate charge
- Improved transconductance
- Low gate drive power loss
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

• APPLICATIONS

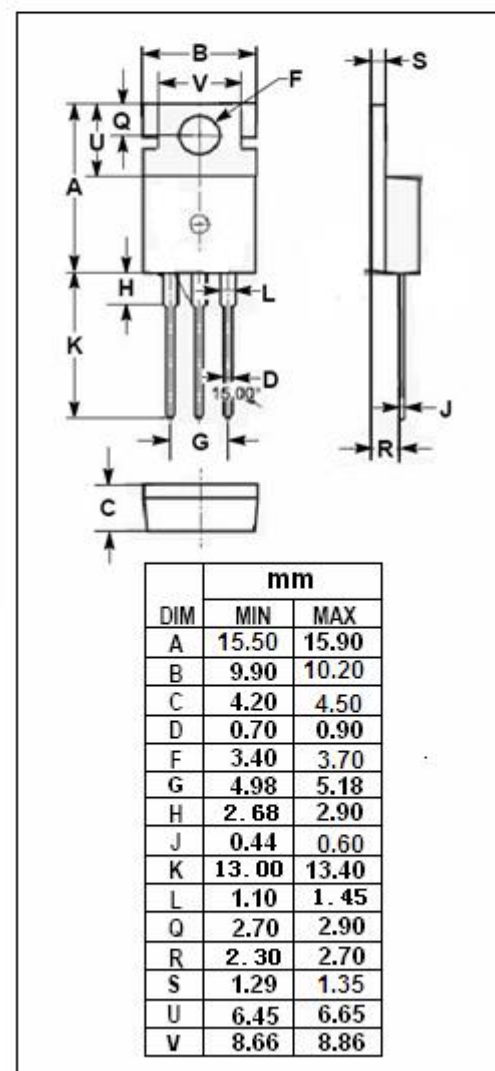
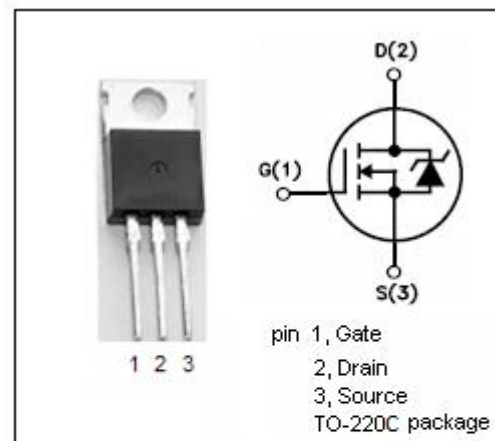
- Switching applications

• ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{DS}	Drain-Source Voltage	800	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous@ $T_c=25^{\circ}\text{C}$ $T_c=100^{\circ}\text{C}$	11 7.1	A
I_{DM}	Drain Current-Single Pulsed	33	A
P_D	Total Dissipation	156	W
T_j	Operating Junction Temperature	-55~150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~150	$^{\circ}\text{C}$

• THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
$R_{th(ch-c)}$	Channel-to-case thermal resistance	0.8	$^{\circ}\text{C/W}$
$R_{th(ch-a)}$	Channel-to-ambient thermal resistance	62	$^{\circ}\text{C/W}$





INCHANGE Semiconductor

Isc N-Channel MOSFET Transistor**SPP11N80C3****ELECTRICAL CHARACTERISTICS** $T_C=25^{\circ}\text{C}$ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP	MAX	UNIT
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$; $I_D=0.25mA$	800			V
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=\pm 20V$; $I_D=0.68mA$	2.1		3.9	V
$R_{DS(on)}$	Drain-Source On-Resistance	$V_{GS}=10V$; $I_D=7.1A$		390	450	$m\Omega$
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$; $V_{DS}=0V$			± 0.1	μA
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=800V$; $V_{GS}=0V$; $T_J=25^{\circ}\text{C}$ $T_J=150^{\circ}\text{C}$			20 200	μA
V_{SDF}	Diode forward voltage	$I_{SD}=11A$, $V_{GS}=0V$			1.2	V